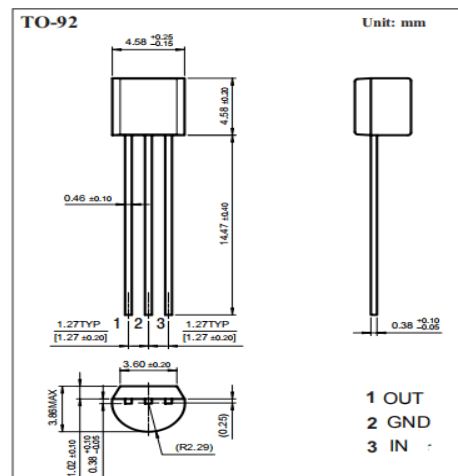


PNP Transistors

2SA1179

■ Features

- High breakdown voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-55	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-150	mA
Collector dissipation	P _C	200	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-50 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = -100μA, I _E = 0A	-55			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = -1mA, I _B = 0 A	-50			V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100μA, I _C = 0A	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -35V, I _E = 0A			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -4V, I _C = 0			-0.1	μA
DC current Gain	h _{FE}	V _{CE} = -6V, I _C = -1mA	200		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -50mA, I _B = -5mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -50mA, I _B = -5mA			-1.0	V
Output capacitance	C _{ob}	V _{CB} = -6V, I _E =0, f = 1MHz		4.0		pF
Transition frequency	f _T	V _{CE} = -6V, I _C = -10mA		180		MHz

■ Marking

Marking	M
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